

IN THE SPECIFICATION

Please replace the paragraph beginning on page 6, line 5, with the following rewritten paragraph:

Turning to the example, the metallization 40 includes a first layer 44 (i.e., a sublayer) that includes titanium or another metal and that is adhered to the substrate 12. On top of the sublayer 44 is a second layer 46 that includes aluminum or aluminum alloy, and aluminum oxide (Al_2O_3). The aluminum alloy may contain copper or magnesium and may form a solid solution (e.g. $Al-Cu$, $Al-Mg$). A next (i.e., third) layer 48 includes an intermetallic compound (e.g., $CuAl_2$, $MgAl_3$). This layer 48 is very thin and is formed by diffusion on the interface between the second layer 46 and the fourth layer 50. An intermediate (i.e., fourth) layer 50 includes a single metal such as copper or magnesium.

Please replace the paragraph beginning on page 6, line 14, with the following rewritten paragraph:

A fifth layer 52 includes an intermetallic compound. The compound may be the same intermetallic compound as the third layer (e.g., $CuAl_2$, $MgAl_3$). A sixth layer 54 includes aluminum or aluminum oxide (Al_2O_3). The solid solution may be the same as the second layer (e.g, $Al-Cu$, $Al-Mg$). Each of the plurality of layers 44-54 has at least a portion (e.g., 48A or 54A) that extends parallel to the planar surface of the substrate 12.

Please replace the chart on page 9, line 26-30, with the following corrected chart:

IDT metal system	PAD/BUSBAR	$R_{IDT}(\text{Ohm})$	$R_{TOT}(\text{Ohm})$	R_{IDT}/R_{TOT}
Al	Al	1.19	9.75	12.2%
Al:2%Cu-Cu-Al:2%Cu	Al:2%Cu-Cu-Al:2%Cu	2.19	18	12.2%
Al	Ag-2 μm	1.17	1.67	70%
Al:2%Cu-Cu-Al:2%Cu	Ag-2 μm	2.19	2.67	82%

Please replace the paragraph beginning on page 13, line 3, with the following rewritten paragraph:

The formation of the silicon dioxide or aluminum oxide top layer 56 is shown in Fig. 10. The removal of the remaining photoresist material 216 at step 116 is schematically shown in Fig. 12.